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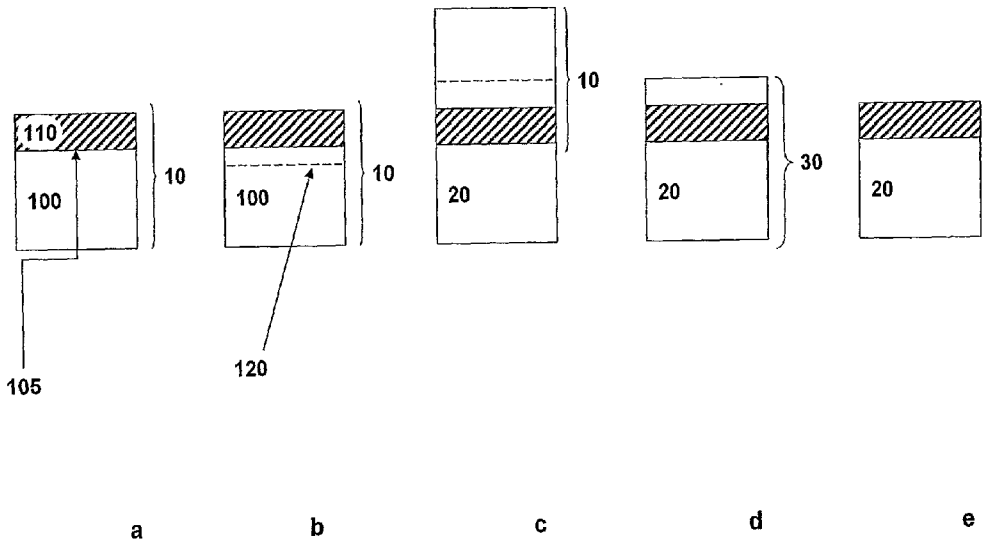
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(54) Title: MANUFACTURING PROCESS FOR A MULTILAYER STRUCTURE



(57) Abstract: The present invention relates to a production process for a multilayer structure made of semiconductor materials, said structure comprising a substrate (20) made of a first semiconductor material and a superficial thin layer made of a second semiconductor material, the two semiconductor materials having substantially different lattice parameters, characterised in that the process comprises the following steps: -producing a layer (110) comprising said superficial thin layer on a support substrate (100), -creating an embrittlement zone in the ensemble (10) formed by said support substrate and said deposited layer, -bonding said ensemble with a target substrate (20), -detaching at the level of this embrittlement zone, -treating the surface of the resulting structure.

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